



JIEJIE MICROELECTRONICS CO., LTD.

Critical rate of rise of on-state current ($I_G=2 I_{GT}$)	dI/dt	125	A s
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33$				

ORDERING INFORMATION

_____ J CT 6 20 A -FO

FIG.1: Maximum power dissipation versus RMS on-state current

$P(w)$

$I_{T(RMS)} (A)$
0 10 20 30 40 50

FIG.2: RMS on-state current versus case temperature

$I_{T(RMS)} (A)$
301

25

20

$T_c (^\circ C)$
0 30 60 90 120 150

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	
------------	----------------------------------	--

PACKAGE MECHANICAL DATA



